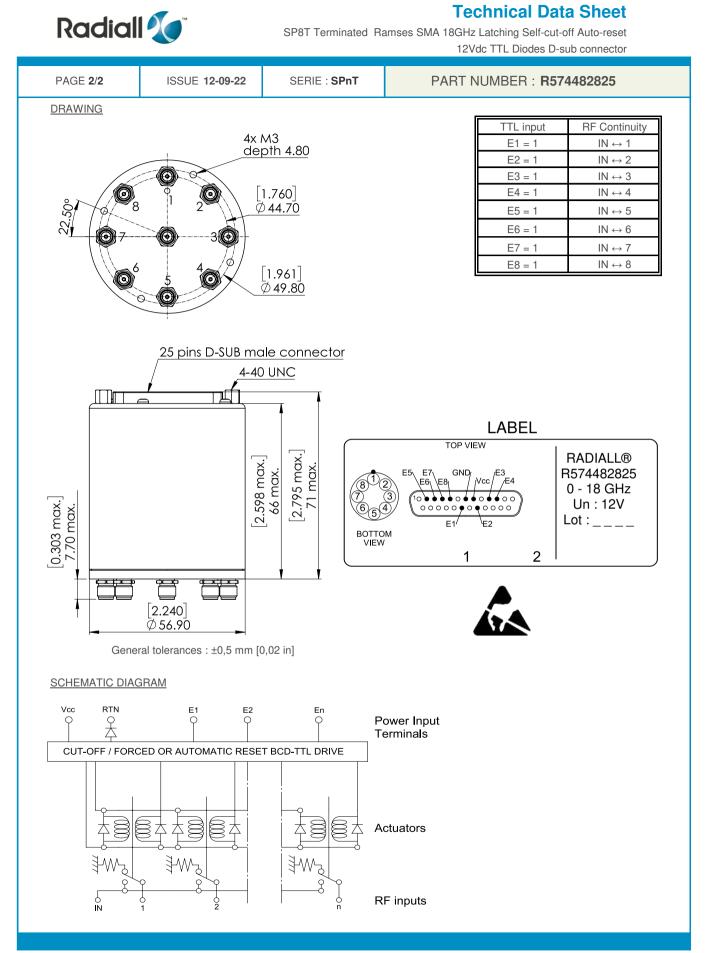


Technical Data Sheet

SP8T Terminated Ramses SMA 18GHz Latching Self-cut-off Auto-reset 12Vdc TTL Diodes D-sub connector

PAGE 1/2 ISSUE		12-09-22 SERIE : SPnT		PART NUMBER : <b>R574482825</b>					
RF C	HARACTERI	<u>STICS</u>							
	Number of w Frequency ra Impedance	-		:	8 0 - 18 GHz 50 Ohms				
	Impedance				50 Onins				
	Frequency (	GHz)	DC - 3	3 - 8	8 - 12.4	12.4 - 16	16 - 18		
	VSWR max		1,20	1,30	1,40	1,50	1,60		
	Insertion los	s max	0.20 dB	0.30 dB	0.40 dB	0.55 dB	0.60 dB		
	Isolation mir Average pov		80 dB 240 W	70 dB 150 W	60 dB 120 W	60 dB 110 W	60 dB 100 W		
	Average por		240 W	150 W	120 W	110 W	100 W		
	TERMINATI	ON IMPEDAI	NCE	:	50 Ohms				
	TERM. AVG	. POWER AT	T 25° C	:	1 W per teri	mination / 3	W total powe	er	
EL EC	CTRICAL CHA	BACTERIST							
			100						
	Actuator			:	LATCHING				
	Nominal cur				960 mA				
	Actuator volt	age (Vcc)			12V (10.2 to				
	Terminals	mo			25 pins D-S		nnector		
Self cut-off time TTL inputs (E) - High level				: 40 ms < CT < 120 ms : 2.2 to 5.5 V / 800μA at 5.5 V					
							5 V		
	TTL inputs (			:	2.2 to 5.5 V	/ 800µA at 5.			
		E) - High		:		/ 800µA at 5.			
		E) - High		:	2.2 to 5.5 V	/ 800µA at 5.			
MEC		E) - High - Low	level	:	2.2 to 5.5 V	/ 800µA at 5.			
MEC	TTL inputs (I	E) - High - Low	level	:	2.2 to 5.5 V 0 to 0.8 V / 2	/ 800µA at 5. 20µA at 0.8 V	1		
MEC	TTL inputs (I	E) - High - Low	level	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female	/ 800µA at 5. 20µA at 0.8 V Э per MIL-C 3	9012		
MEC	TTL inputs (I HANICAL CH Connectors Life	E) - High - Low <u>ARACTERIS</u>	level	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy	/ 800µA at 5. 20µA at 0.8 V Э per MIL-C 3	9012		
MEC	TTL inputs (I HANICAL CH Connectors Life Switching Ti	E) - High - Low <u>ARACTERIS</u> me***	level	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
MEC	TTL inputs (I HANICAL CH Connectors Life	E) - High - Low <u>ARACTERIS</u> me***	level	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
MEC	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction	E) - High - Low <u>ARACTERIS</u> me***	level	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight	E) - High - Low <u>ARACTERIS</u> me***	level <u>TICS</u>	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction	E) - High - Low <u>ARACTERIS</u> me***	level <u>TICS</u>	:	2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight	E) - High - Low ARACTERIS	Ievel TICS ERISTICS		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 № e per MIL-C 3 cles per pos	9012		
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAL	E) - High - Low ARACTERIS me***	Ievel TICS ERISTICS		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012		
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAL	E) - High - Low ARACTERIS	Ievel TICS ERISTICS		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012	ROHS	
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAL	E) - High - Low ARACTERIS me***	Ievel TICS ERISTICS		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012	RoHS	
	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAL	E) - High - Low ARACTERIS me***	level <u>TICS</u> ERISTICS unge ge		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012	RoHs	
<u>ENVI</u>	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAL	E) - High - Low ARACTERIS me*** - CHARACTE mperature rang perature rang	level <u>TICS</u> ERISTICS unge ge		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012		
<u>ENVI</u> (*	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight IRONMENTAI Operating te Storage tem Average pov	E) - High - Low ARACTERIS me*** - CHARACTE mperature rangerature r	level <u>TICS</u> ERISTICS unge ge		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012	ROHS COMPLIAN	
<u>ENVI</u> (* (**	TTL inputs (I HANICAL CH Connectors Life Switching Ti Construction Weight RONMENTAL Operating te Storage tem Average pov At 25° C ±10	E) - High - Low ARACTERIS me*** - CHARACTE mperature rangerature r	level <u>TICS</u> ERISTICS unge ge		2.2 to 5.5 V 0 to 0.8 V / 2 SMA female 2 million cy < 50 ms Splashproo < 280 g	/ 800µA at 5. 20µA at 0.8 V e per MIL-C 3 cles per pos of 5°C	9012		

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